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November 2013

# FDP12N50 / FDPF12N50T N-Channel UniFET<sup>TM</sup> MOSFET 500 V, 11.5 A, 650 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 550 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 6 A
- Low Gate Charge (Typ. 22 nC)
- Low C<sub>rss</sub> (Typ. 11 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

## **Applications**

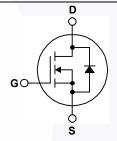
- LCD/LED/PDP TV
- · Lighting
- · Uninterruptible Power Supply

## Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

| Symbol                            |                       | Parameter                                  |              | FDP12N50 | FDPF12N50T | Unit |
|-----------------------------------|-----------------------|--|--------------|----------|------------|------|
| $V_{DSS}$                         | Drain to Source Volta | ource Voltage                              |              |          | 00         | V    |
| $V_{GSS}$                         | Gate to Source Volta  | Source Voltage                             |              |          | 30         | V    |
|                                   | Drain Current         | - Continuous (T <sub>C</sub> = 25°C)       |              | 11.5     | 11.5 *     | Α    |
| ID                                | DrainGuilent          | - Continuous (T <sub>C</sub> = 100°C)      | )            | 6.9      | 6.9 *      | Α    |
| I <sub>DM</sub>                   | Drain Current         | - Pulsed                                   | (Note 1)     | 46       | 46 *       | Α    |
| E <sub>AS</sub>                   | Single Pulsed Avalar  | nche Energy                                | (Note 2)     | 4        | 56         | mJ   |
| I <sub>AR</sub>                   | Avalanche Current     |  | (Note 1)     | 1        | 1.5        | Α    |
| E <sub>AR</sub>                   | Repetitive Avalanche  | e Energy                                   | (Note 1)     | ) 16.7   |            | mJ   |
| dv/dt                             | Peak Diode Recover    | y dv/dt                                    | (Note 3)     | 4        | l.5        | V/ns |
| D                                 | Dower Dissination     | (T <sub>C</sub> = 25°C)                    |              | 165      | 42         | W    |
| $P_{D}$                           | Power Dissipation     | - Derate Above 25°C                        |              | 1.33     | 0.3        | W/°C |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Stora   | ing and Storage Temperature Range          |              |          | o +150     | οС   |
| TL                                | Maximum Lead Tem      | perature for Soldering, 1/8" from Case for | or 5 Seconds | 3        | 00         | οС   |

<sup>\*</sup>Drain current limited by maximum junction temperature

#### **Thermal Characteristics**

| Symbol          | Parameter                                     | FDP12N50 | FDPF12N50T | Unit  |
|-----------------|---|----------|------------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max.    | 0.75     | 3.0        | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 62.5     | 62.5       | *C/VV |

## **Package Marking and Ordering Information**

| Part Number | Top Mark   | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|------------|---------|----------------|-----------|------------|----------|
| FDP12N50    | FDP12N50   | TO-220  | Tube           | N/A       | N/A        | 50 units |
| FDPF12N50T  | FDPF12N50T | TO-220F | Tube           | N/A       | N/A        | 50 units |

## **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted.

| Symbol                                  | Parameter                                    | Test Conditions                                       | Min. | Тур. | Max. | Unit |
|---|--|---|------|------|------|------|
| Off Charac                              | cteristics                                   |   |      |      |      |      |
| BV <sub>DSS</sub>                       | Drain to Source Breakdown Voltage            | $I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$   | 500  | -    | -    | V    |
| ΔBV <sub>DSS</sub><br>/ ΔT <sub>J</sub> | Breakdown Voltage Temperature<br>Coefficient | $I_D$ = 250 μA, Referenced to 25°C                    | -    | 0.5  | -    | V/°C |
| 1                                       | Zero Gate Voltage Drain Current              | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V        | -    | -    | 1    | ^    |
| IDSS                                    | Zero Gate Voltage Drain Current              | $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$ | -    | -    | 10   | μΑ   |
| I <sub>GSS</sub>                        | Gate to Body Leakage Current                 | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$     | -    | -    | ±100 | nA   |

#### **On Characteristics**

| V <sub>GS(th)</sub> | Gate Threshold Voltage               | $V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$   | 3.0 | -    | 5.0  | V |
|---------------------|--------------------------------------|--|-----|------|------|---|
| R <sub>DS(on)</sub> | Static Drain to Source On Resistance | $V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$   | -   | 0.55 | 0.65 | Ω |
| 9 <sub>FS</sub>     | Forward Transconductance             | V <sub>DS</sub> = 40 V, I <sub>D</sub> = 6 A | ı   | 11.5 | ı    | S |

## **Dynamic Characteristics**

| C <sub>iss</sub> | Input Capacitance             | V - 25 V V - 0 V  |          | -   | 985 | 1315 | pF |
|------------------|-------------------------------|---|----------|-----|-----|------|----|
| C <sub>oss</sub> | Output Capacitance            | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$<br>f = 1 MHz |          | -\  | 140 | 190  | pF |
| C <sub>rss</sub> | Reverse Transfer Capacitance  | 1 = 1 101112  |          | - \ | 11  | 17   | pF |
| $Q_g$            | Total Gate Charge at 10V      | V <sub>DS</sub> = 400 V, I <sub>D</sub> = 11.5 A,           |          | - \ | 22  | 30   | nC |
| $Q_{gs}$         | Gate to Source Gate Charge    | V <sub>GS</sub> = 10 V                                      |          | -   | 6   | -    | nC |
| $Q_{gd}$         | Gate to Drain "Miller" Charge |   | (Note 4) | -   | 9   | -    | nC |

## **Switching Characteristics**

| t <sub>d(on)</sub>  | Turn-On Delay Time  |   | - | 24 | 60  | ns |
|---------------------|---------------------|---|---|----|-----|----|
| t <sub>r</sub>      |                     | $V_{DD} = 250 \text{ V}, I_D = 11.5 \text{ A},$ | - | 50 | 110 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time | $V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$            | - | 45 | 100 | ns |
| t <sub>f</sub>      | Turn-Off Fall Time  | (Note 4)  | - | 30 | 70  | ns |

#### **Drain-Source Diode Characteristics**

| ls              | Maximum Continuous Drain to Source Dioc | Maximum Continuous Drain to Source Diode Forward Current |   | -   | 11.5 | Α  |
|-----------------|---|--|---|-----|------|----|
| I <sub>SM</sub> | Maximum Pulsed Drain to Source Diode Fo | orward Current   | - | -   | 46   | Α  |
| $V_{SD}$        | Drain to Source Diode Forward Voltage   | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 11.5 A          | - | -   | 1.4  | V  |
| t <sub>rr</sub> | Reverse Recovery Time                   | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 11.5 A,         | - | 375 | -    | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                 | $dI_F/dt = 100 A/\mu s$                                  | - | 3.5 | -    | μС |

#### Notes

- ${\it 1. Repetitive\ rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.}$
- 2. L = 6.9 mH, I<sub>AS</sub> = 11.5 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3.  $I_{SD} \le 11.5$  A, di/dt  $\le 200$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

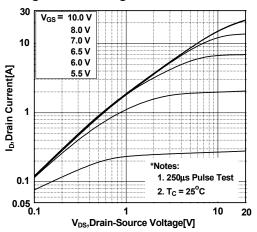


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

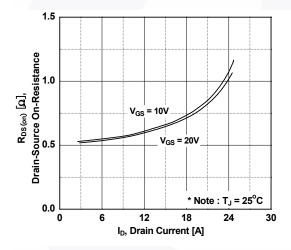


Figure 5. Capacitance Characteristics

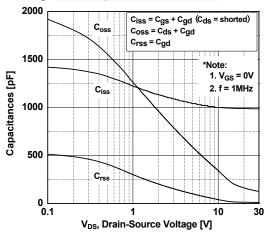


Figure 2. Transfer Characteristics

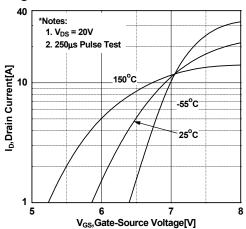


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

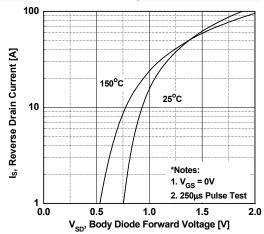
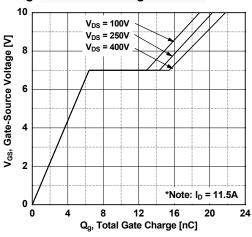


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

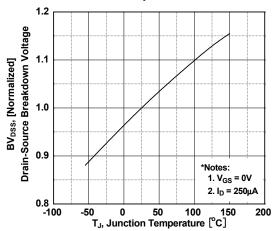


Figure 9-1. Maximum Safe Operating Area - FDP12N50

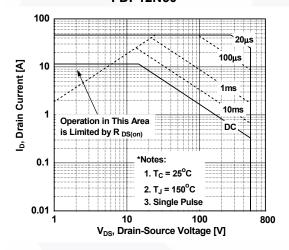


Figure 8. On-Resistance Variation vs. Temperature

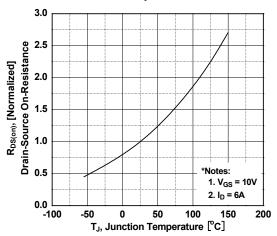


Figure 9-2. Maximum Safe Operating Area - FDPF12N50T

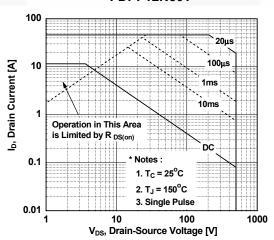
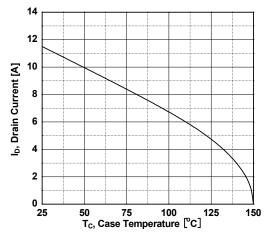


Figure 10. Maximum Drain Current vs. Case Temperature



## **Typical Performance Characteristics** (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP12N50

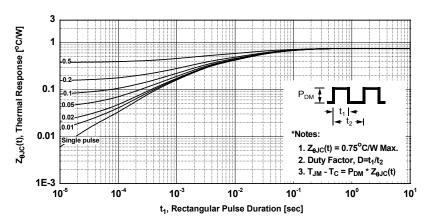
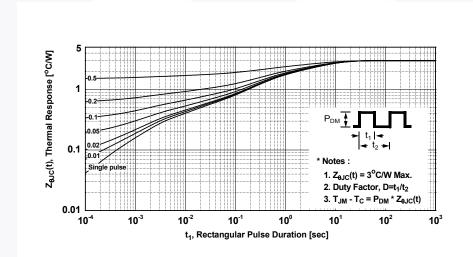


Figure 11-2. Transient Thermal Response Curve - FDPF12N50T



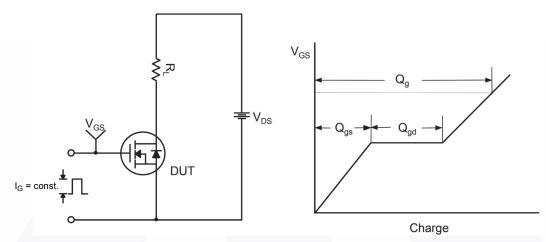


Figure 12. Gate Charge Test Circuit & Waveform

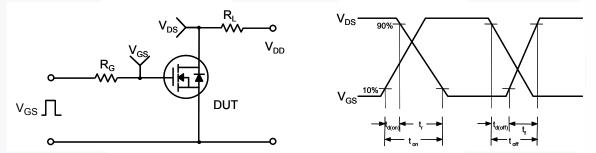


Figure 13. Resistive Switching Test Circuit & Waveforms

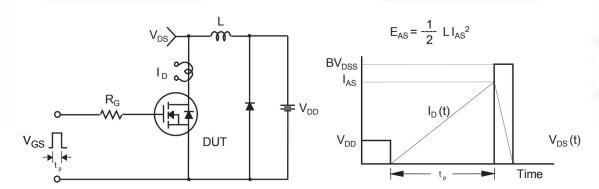


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

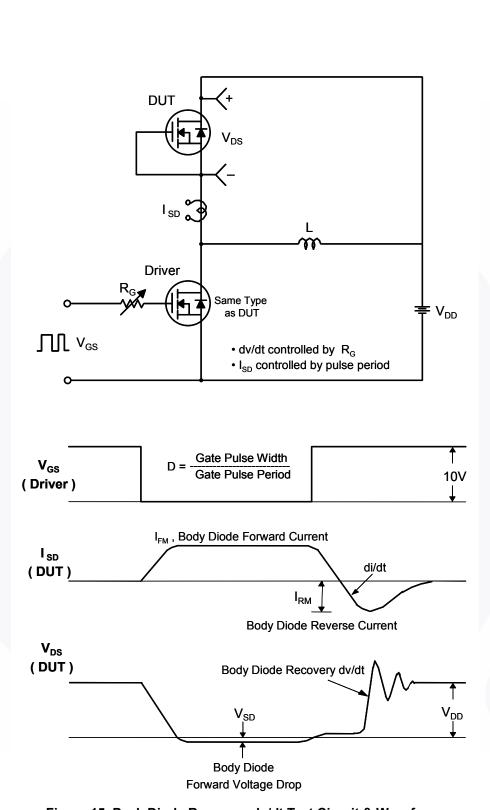


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

## **Mechanical Dimensions**

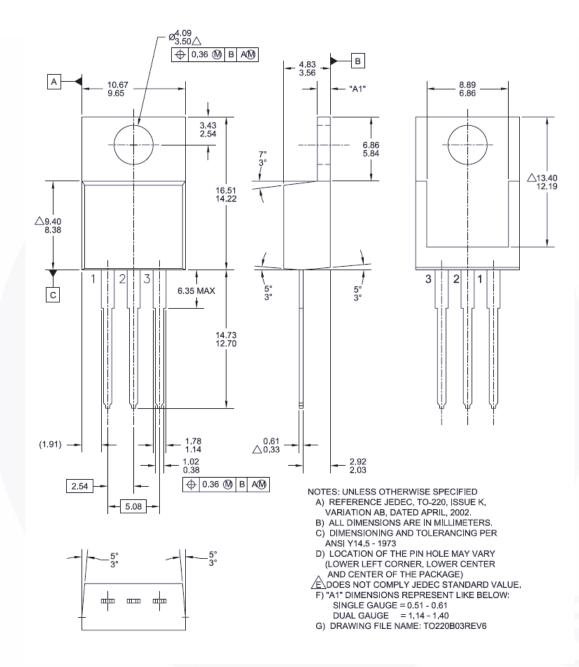


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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## **Mechanical Dimensions**

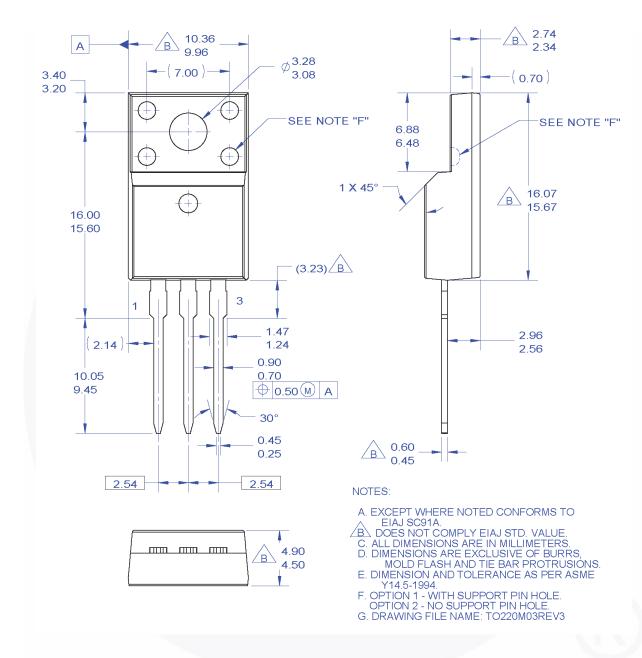


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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